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# Melting and crystallization features of CsPbBr<sub>3</sub> perovskite

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KEYWORDS: CsPbBr<sub>3</sub>, melting, crystallization, Phase transition, heating/cooling rate

## ABSTRACT

All-inorganic perovskite CsPbBr<sub>3</sub> has attracted considerable attention as a promising material for optoelectronics and high-energy radiation detectors. In order to obtain a bulk single crystal from a

melt, it is crucial to understand the peculiarities of melting and crystallization processes. Here, the solid-liquid and liquid-solid phase transitions were studied by differential thermal analysis (DTA) at different heating/cooling rates (0.1, 1, 3, 5, and 10 °C/min). A two-stage melting mechanism of CsPbBr<sub>3</sub> perovskite was proposed. A critical maximal sample temperature ( $T_{\text{critical}}$ ) was determined for each heating rate. If the sample was heated to a temperature below  $T_{\text{critical}}$ , the crystallization occurred at a higher temperature than the melting point. Contrary, if the sample was heated to a temperature higher than this critical value, the melt crystallization occurred with supercooling. We believe that such crystallization features are closely related to the melt structure, which changes during the sample heating. The activation energies of melting and crystallization processes of CsPbBr<sub>3</sub> were determined as 1846 kJ/mol and 1940 kJ/mol, respectively. For the first time, this study demonstrates the impact of heating and cooling conditions on the melting and crystallization processes of the bulk CsPbBr<sub>3</sub>. It is significant for fundamental crystal growth understanding and fabrication of high-quality monocrystalline material.

## INTRODUCTION

All-inorganic CsPbBr<sub>3</sub> semiconductor perovskite attracts a lot of attention nowadays. This material is very promising for use in lasers,<sup>1-2</sup> for manufacturing photodetectors,<sup>3-7</sup> X- and  $\gamma$ -rays detectors,<sup>8-12</sup> and solar cells.<sup>13-16</sup> Despite the wide use of low dimensional CsPbBr<sub>3</sub> in the form of nanocrystals, nanowires, and polycrystalline thin films, CsPbBr<sub>3</sub> single crystals represent the most stable form of this material. Bulk single crystals better represent the fundamental physical properties of CsPbBr<sub>3</sub> and can be more easily applied for the fabrication of photo- and ionizing radiation detectors. Crystals can be obtained by the solution growth method,<sup>9, 17-18</sup> but in this case, the crystal matrix may capture solvent molecules, which affects its optical and electrical properties.<sup>9,17</sup> The optimal way to obtain cesium lead bromide crystals is the growth from the

melt.<sup>7,8,10,19</sup> This method allows obtaining large in diameter single crystals with stoichiometric composition and excellent quality without organic contaminants. To grow high-quality perovskite single crystals from the melt, it is necessary to clearly understand the melting mechanism of the CsPbBr<sub>3</sub> and, even more importantly, the crystallization mechanism. Although the first work on CsPbBr<sub>3</sub> dates back to the late 19th century,<sup>20</sup> and the early investigations of the cesium lead bromide structure were carried out in the middle of the 20th century,<sup>21,22</sup> to the best of our knowledge, there are no studies on the melting and crystallization processes of the bulk CsPbBr<sub>3</sub>. In several works,<sup>23-25</sup> authors studied low-temperature structural transformations of CsPbBr<sub>3</sub> by various methods such as neutron diffraction method, differential scanning calorimetry, thermomechanical analysis, and high-temperature X-ray diffraction, but there is minor data on solid-liquid phase transitions for CsPbBr<sub>3</sub>. Cola et al.<sup>26</sup> investigated the CsBr – PbBr<sub>2</sub> system by differential thermal analysis (DTA) and found that the stoichiometric compound of CsPbBr<sub>3</sub> melts congruently at 567 °C. In more recent works<sup>8,19,27</sup> DTA method was used as a tool for melting point determination without explanations of regularities in the melting and crystallization processes of CsPbBr<sub>3</sub>. The melting point was mentioned as 567 °C, but crystallization temperature varied from 514 °C<sup>8</sup> to 550-555 °C.<sup>19,27</sup> Those variations are probably due to the inconsistency in experimental conditions and different heating and cooling rates used during the measurements. In this work, we carried out the systematic study of melting and crystallization processes of all-inorganic CsPbBr<sub>3</sub> perovskite and described its phase transitions mechanism.

## **EXPERIMENTAL SECTION**

### **Materials**

Commercially available cesium bromide CsBr (99.9999%) and lead (II) bromide PbBr<sub>2</sub> (99.999%) were purchased from Sigma-Aldrich.

### **CsPbBr<sub>3</sub> powder synthesis and polycrystal growth**

The synthesis of all-inorganic perovskite CsPbBr<sub>3</sub> was carried out by the mechanochemical method<sup>8</sup>. An equimolar quantity of CsBr and PbBr<sub>2</sub> was carefully ground and mixed in a mortar with a pestle at room temperature. Immediately after mixing began, the color of the powder gradually changed from white to saturated orange, indicating a solid-state synthesis reaction. 20 g of obtained CsPbBr<sub>3</sub> powder was loaded into a quartz ampoule, evacuated to 10<sup>-4</sup> mbar, and sealed. Then the ampoule was placed in a furnace and heated to 640 °C, exceeding the cesium bromide melting point. At this temperature, the melt was held for several hours and then cooled to room temperature for 20 hours.

### **X-ray Diffraction (XRD) measurements**

X-ray diffraction analysis was performed by classical ex-situ Bragg – Brentano geometry using a PANalytical X'pert powder diffractometer with filtered Cu-K $\alpha$  radiation and an X'Celerator solid-state stripe detector. For measurements, polycrystalline CsPbBr<sub>3</sub> was ground into powder and placed on a zero background silicon wafer.

### **Differential thermal analysis (DTA)**

500 mg of CsPbBr<sub>3</sub> sample for the DTA experiment was loaded into a specially designed quartz ampoule (Supporting Information Figure S1a) and sealed under 10<sup>-4</sup> mbar pressure. Measurements are performed on an in-house-built automated DTA setup with S-type thermocouples (Figure S1b). During experiments, the heating/cooling of samples was performed at different rates: 0.1, 1, 3, 5, and 10 °C/min, respectively. Measurements were carried out cyclically. The first cycle was started from room temperature, but all following cycles were performed starting from 450 °C. During recurring heatings and coolings, the maximal sample temperature increased step by step from the melting point of cesium lead bromide to ~590 °C. We fixed the melting and crystallization

temperature of CsPbBr<sub>3</sub> and temperatures of minimum and maximum on peaks on the thermograms in each cycle. The time of these points on thermograms was also recorded. Every measurement was repeated thrice.

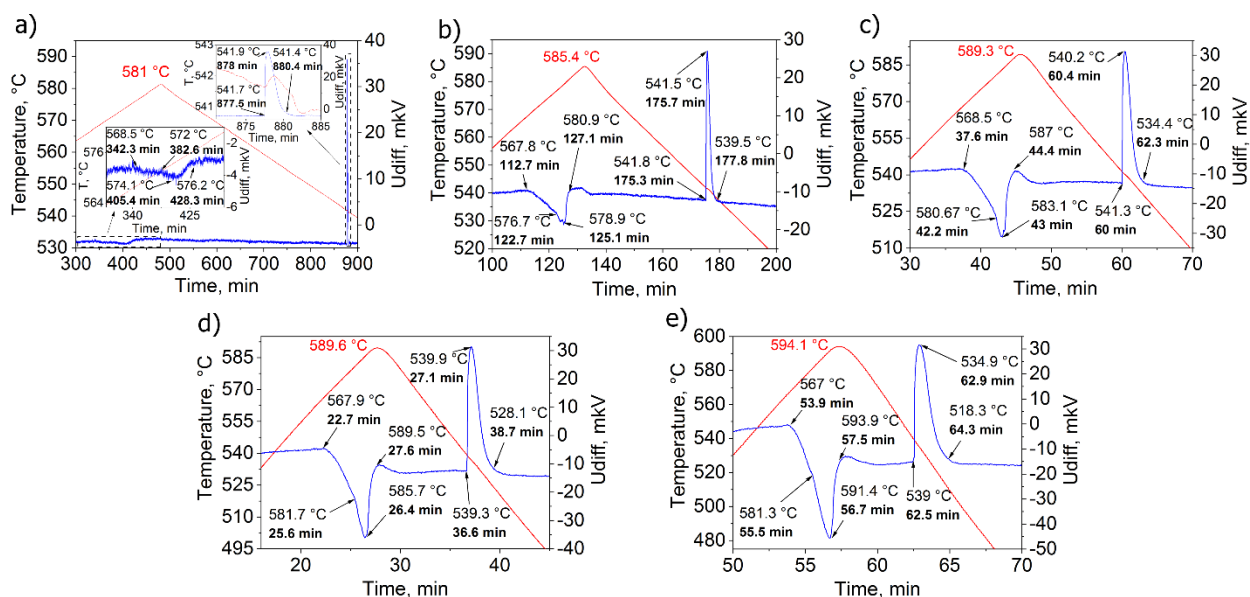
## RESULTS AND DISCUSSION

Obtained polycrystalline cesium lead bromide was investigated using an XRD-analysis, which confirmed the perovskite orthorhombic crystalline structure (Figure S2.).

During the DTA experiment at different conditions, we determined the melting and crystallization temperature of CsPbBr<sub>3</sub> by a baseline bend on the thermograms (Figure 1). In all cases melting point was in the range from 567 to 568.5 °C, which is in good agreement with previously published data.<sup>8,19,26,27</sup> Considering in detail the process of perovskite melting, we have observed the phase transition that occurs differently on the different heating rates. In particular, it is related to the melting process duration. In the case of heating rate 0.1 °C / min, the process takes about 60 min. In the heating rate of 1 °C/min, the melting process duration was about ~ 12 min and decreased to ~ 3 min with an increase in heating rate up to 10 °C/min. The melting process duration was determined on thermograms as a difference between melting peak minimum time and baseline bend time, indicating the melting process's start. Based on these results, it can be assumed that the melting process of CsPbBr<sub>3</sub> is not isothermal, and it occurs within a specific temperature range. Depending on heating conditions, this range may change from interval of 567-574 °C for 0.1 °C/min to 567-591 °C for 10 °C/min. Slow heating rate (0.1 °C/min), which is closest to equilibrium conditions (Fig. 1 a), clearly shows that the endothermic melting peak is stretched in time, but it is less pronounced than in cases with faster heating (Fig. 1 b-e).

Particular attention should be paid to an additional slope on the melting peak on the thermograms, which is present in all cases. We can see some changes in the starting temperature

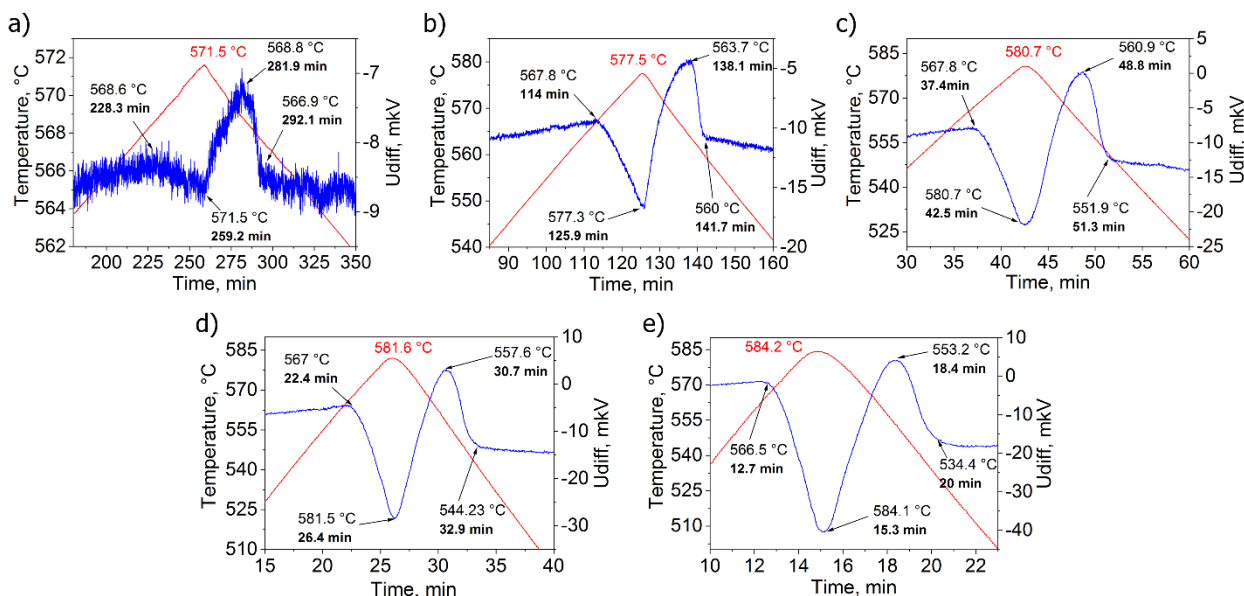
of this slope. Thus, it is fixed at 572 °C and 577 °C at the heating rates of 0.1 °C/min and 1 °C/min respectively. As the heating rate increases to 3, 5, and 10 °C/min, this temperature shifts to ~581 °C and keep constant. Change in the curvature of the line in differential thermocouple signal record during the melting process may indicate a two-step melting mechanism of CsPbBr<sub>3</sub> perovskite. It can be similar to other semiconductors such as CdTe or Cd(Zn)Te, when the solid phase fragmentation first occurs and then, with continued heating, the melting of these residues of the crystalline structure predominates.<sup>28,29</sup> After that, the melt becomes homogenous.



**Figure 1.** Melting and crystallization thermograms of CsPbBr<sub>3</sub> at different heating / cooling rates: a) 0.1 °C/min; b) 1 °C/min; c) 3 °C/min; d) 5 °C/min; e) 10 °C/min. Red lines represent temperature changes during measurements and blue lines – the differential thermocouple voltage record.

The heating/cooling rate and melting process features have a direct impact on the sample crystallization process. Figure 1a-e represents the peculiarities of the CsPbBr<sub>3</sub> melting and crystallization processes in the conditions when the sample was heated above the melting point (567-568 °C) by ~15-20 °C, and the melting process was completed (record of the full melting peak on thermograms). Another situation is when the melting process was incomplete during the

heating (record of the incomplete melting peak on thermograms). In that case, the melt crystallizes at the same temperature from which the sample cooling was started (Figure 2).



**Figure 2.** Melting and crystallization thermograms of CsPbBr<sub>3</sub> with low superheating at different heating/cooling rates: a) 0.1 °C/min; b) 1 °C/min; c) 3 °C/min; d) 5 °C/min; e) 10 °C/min. Red lines represent temperature changes during measurements, blue lines – the differential thermocouple voltage record.

In that case, we observed a "hot" crystallization when the temperature of the crystallization start point is higher than the point of the melting start. It is in good agreement with the two-stage mechanism of melting proposed above. Fragments of solid-phase which are present in the melt become centers of crystallization and promote the crystallization process immediately after the start of cooling. It is typical for all investigated heating rates from 0.1 °C / min to 10 °C / min with a low superheating degree. On the other hand, if heating continues to higher temperatures, we get an opposite situation when the melt crystallizes with supercooling when sample cooling (Figure 3). The crystallization temperature of CsPbBr<sub>3</sub> is weakly dependent on the maximum sample

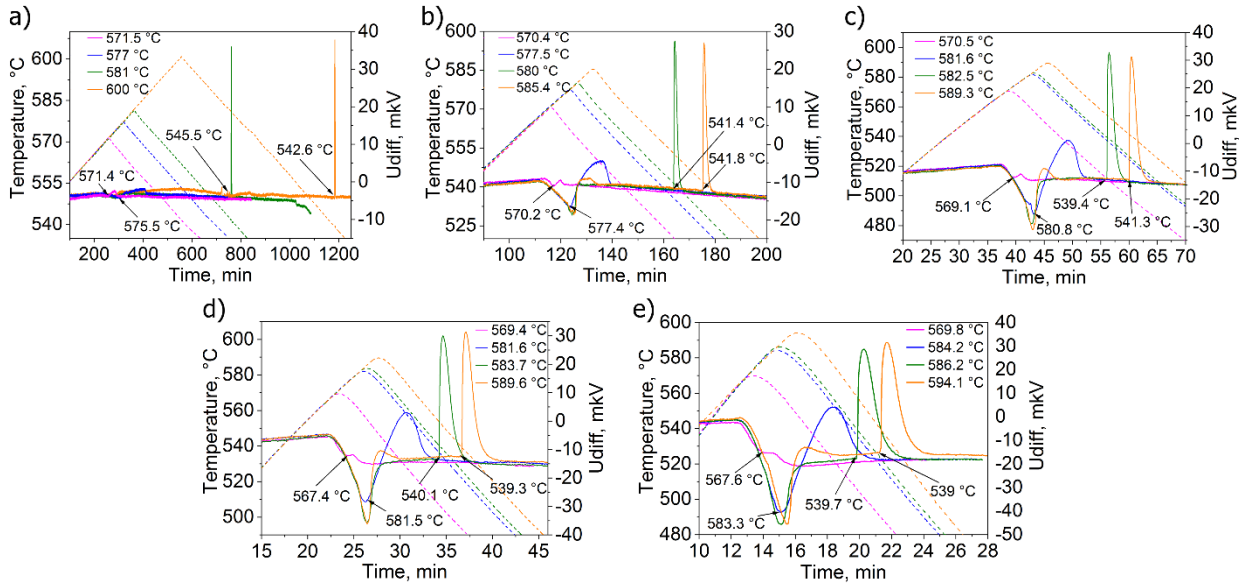


temperature and heating rate if superheating achieves a specific defined value. This value of maximal sample temperature we called "critical temperature" ( $T_{critical}$ ), after which the melt of the perovskite crystallizes in a narrow range temperature with practically permanent supercooling. In Figure 3, the melt crystallization in such conditions characterizes by complete exothermic peaks, which observes at around 539-545 °C. These peaks are clearly separated in time from melting peaks depending on the heating rate and the superheating degree. Here is necessary to specify superheating ( $\Delta T^+$ ), which we have calculated as a difference between the maximal sample temperature ( $T_{max}$ ) and temperature when melting of the sample starts ( $T_{melt}$ ):

$$\Delta T^+ = T_{max} - T_{melt} \quad (1)$$

and supercooling ( $\Delta T^-$ ), which was calculated as a difference between the melting start temperature and crystallization start temperature ( $T_{cryst}$ ):

$$\Delta T^- = T_{melt} - T_{cryst} \quad (2)$$

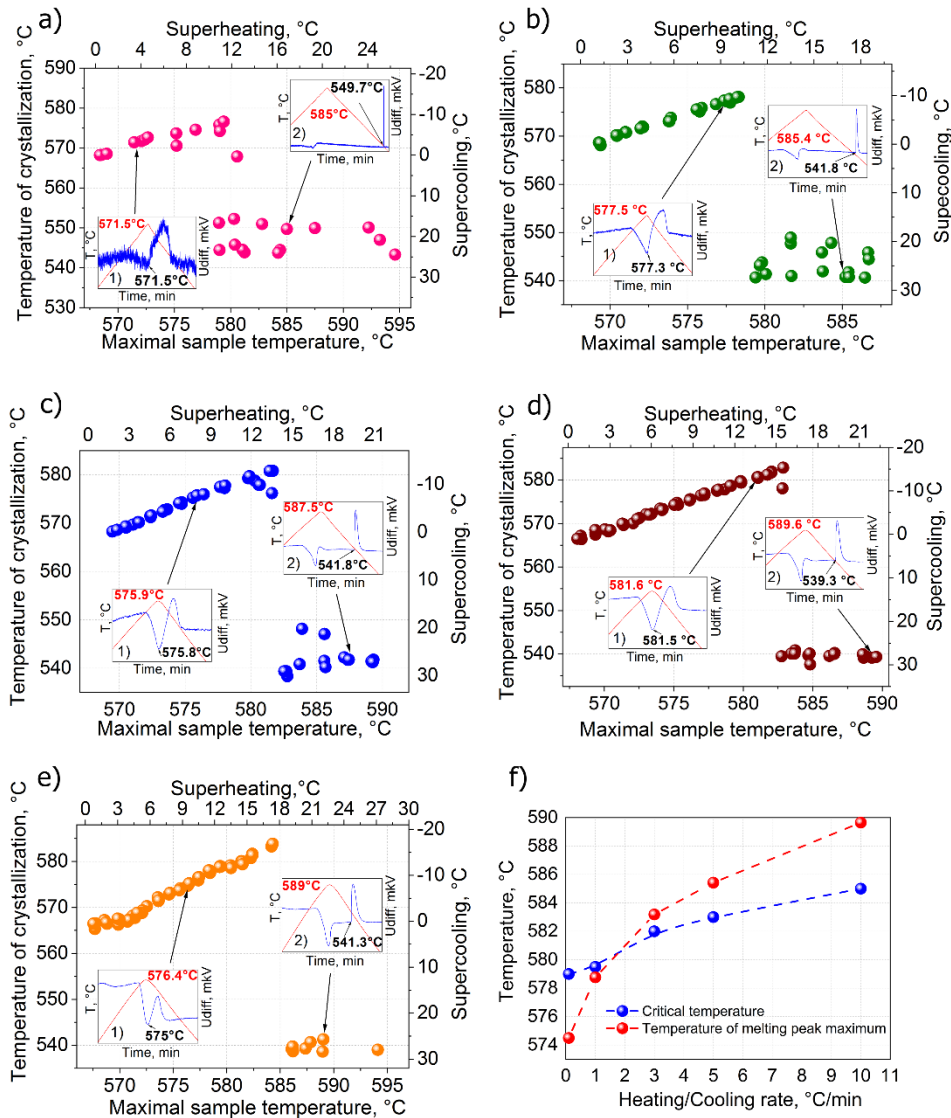


**Figure 3.** Melting/crystallization thermograms of CsPbBr<sub>3</sub> at different maximal sample temperature with heating rates: a) 0.1 °C / min., b) 1 °C / min., c) 3 °C / min., d) 5 °C/min.;

e) 10 °C/min. The peaks on the dashed lines indicate the maximal temperatures of the sample during experiments. Solid lines on all graphs are the differential thermocouple voltage records.

The temperature of CsPbBr<sub>3</sub> melt crystallization gradually increases from 568 °C to 577 °C in the case if the sample was heated to a temperature in the range from melting point temperature (~567-568 °C) to 579 °C at a heating/cooling rate of 0.1 °C/min (Figure 4a). At the same time, superheating increases, and crystallization of CsPbBr<sub>3</sub> melt occurs with supercooling in the range from 0 °C to -9 °C ("hot" crystallization). With further heating to higher temperatures, a dramatic decrease in crystallization temperature was observed. The oscillation of crystallization temperature from 543 °C to 552 °C took place when the sample was heated to a temperature greater than 579 °C. It corresponds to melt supercooling in the range from 16 °C to 25 °C. In the range of small superheating temperatures, the melting of perovskite is incomplete, and the start of the melt crystallization process is indistinct, as shown on thermograms (Figure 4a-1). It can be explained as follows: in the melt are present solid-phase fragments of different sizes, the number of which increases while approaching the critical temperature. It is caused by the splitting of large solid fragments into smaller ones. These structural units in the melt are acting as crystallization centers and trigger premature melt solidification ("hot" crystallization). After overcoming the critical superheating temperature (579 °C), CsPbBr<sub>3</sub> melts completely, and the melt becomes homogenous. Melt crystallization under these conditions is clearly shown on thermograms with supercooling (Figure 4a-2) as described above. We can also observe similar dependencies in the case of faster heating/cooling rates (Figure 4b-e). The temperature intervals of melt crystallization with supercooling are 540-550 °C for  $V_{h/c} = 1$  °C/min, 538-543 °C for  $V_{h/c} = 3$  °C/min, 537-542 °C for  $V_{h/c} = 5$  °C/min, and 538-542 °C for  $V_{h/c} = 10$  °C/min.. However, with increasing in the heating/cooling rate, a shift in  $T_{critical}$  was observed. In the case of heating/cooling rate of 1 °C/min,

the same  $T_{\text{critical}}$  was observed similar to  $0.1\text{ }^{\circ}\text{C}/\text{min}$ , but with  $V_{h/c} = 3, 5$  and  $10\text{ }^{\circ}\text{C}/\text{min}$   $T_{\text{critical}}$  was recorded as  $582\text{ }^{\circ}\text{C}$ ,  $583\text{ }^{\circ}\text{C}$ , and  $585\text{ }^{\circ}\text{C}$  respectively (Figure 4c-e). We believe that is due to the kinetic regularities of the melting process. According to the differential thermal analysis theory,<sup>30</sup> melting peaks minimums on thermograms indicate full completion of the endothermic melting process. Increasing the heating rate leads to an increase of the temperatures of minimums these peaks.<sup>30,31</sup> The shift in critical temperature ( $T_{\text{critical}}$ ) co-occurs with an increase of the temperature of melting peak minimum on thermograms (Figure 4f) and is apparently caused by the same kinetic patterns.

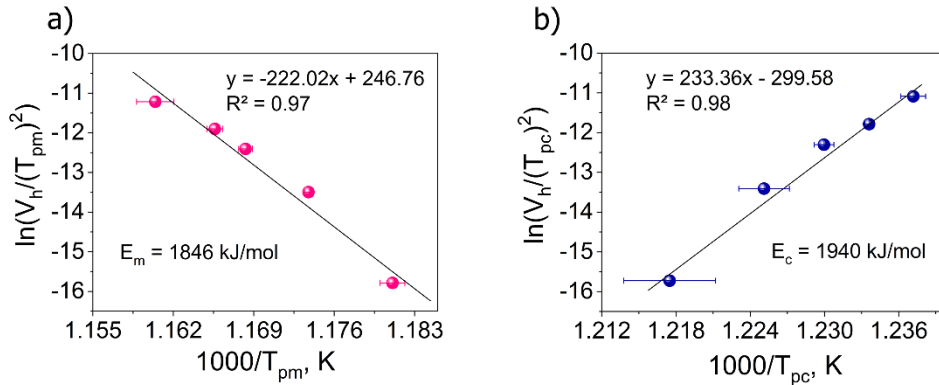


**Figure 4.** Dependences of the crystallization temperature of the CsPbBr<sub>3</sub> melt versus the maximal sample temperature and supercooling versus superheating at different heating/cooling rates: a) 0.1 °C / min., b) 1 °C / min., c) 3 °C / min., d) 5 °C/min.; e) 10 °C/min. Inserted thermograms 1) and 2) illustrate the melt crystallization with different superheating degrees (See Figure 1 and Figure 2); f) - Change in critical temperature and temperature of melting peak minimum depending on the heating rate.

Using data from thermograms after  $T_{\text{critical}}$  (with complete melting and crystallization peaks) with different heating/cooling rates, the activation energy of the CsPbBr<sub>3</sub>, melting  $E_m$ , and crystallization  $E_c$  processes were estimated. Activation energy is associated with heating rates, according to the Kissinger equation:<sup>32,33</sup>

$$\ln \frac{V_h}{T_p^2} = \text{const} + \frac{E_a}{RT_p} \quad (3)$$

where  $V_h$  is the heating/cooling rate,  $T_p$  is the melting peak minimum or crystallization peak maximum temperature on thermograms, and  $R$  is the universal gas constant. The slope of a straight line in coordinates  $\ln(V_h/T_p^2)$  vs  $1000/T_p$  (Figure 5) is equal to  $E/R$ . The calculated values of activation energy for melting and crystallization processes were 1846 kJ/mol and 1940 kJ/mol, respectively. As we can see, both values are comparable.



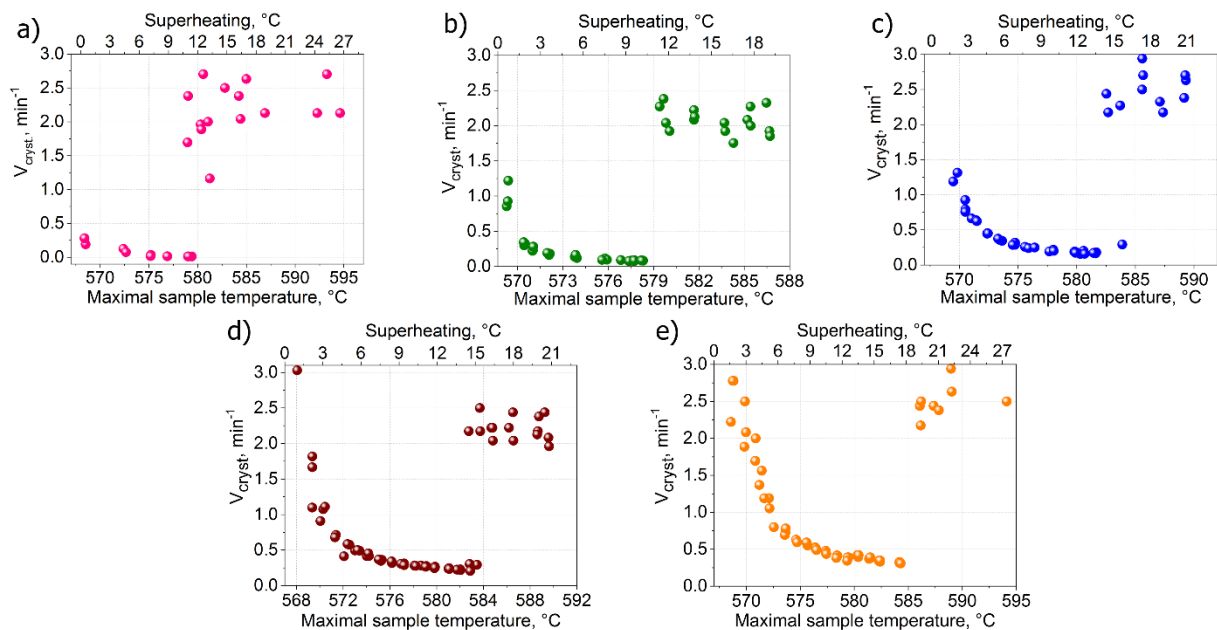
**Figure 5.** The Kissinger plots of CsPbBr<sub>3</sub> melting (a) and crystallization (b) processes. The values of the peak temperatures  $T_p$  were taken from DTA thermograms with different heating/cooling rates.

Considering in more detail the crystallization process of CsPbBr<sub>3</sub> at different heating/cooling rates, we should consider the dependencies of crystallization rates ( $V_{cryst}$ ) on temperatures to which the melt was heated before cooling down. The crystallization rate is inversely proportional to the duration of the crystallization process. It can be estimated as a reverse value of the difference between the time of crystallization peak maximum  $t_{cryst}^{peak}$  and the start time of the crystallization process  $t_{cryst}^{start}$ .<sup>34,35</sup>

$$V_{cryst} = \frac{1}{t_{cryst}^{peak} - t_{cryst}^{start}} \quad (4)$$

Figure 6 clearly shows the sharp jump of melt crystallization rate occurring at the critical temperature at all heating/cooling rates. The crystallization rate smoothly decreases in the temperature range from slight superheating ( $\sim 1$  °C) to critical temperatures. It was observed for all investigated cooling rates, but it is getting more pronounced with faster cooling. In small superheating, large in size residues of the crystalline phase are present in the melt and promote fast crystallization. The logical consequence is the presence of a small amount of the liquid phase in the system under these conditions. It can be evaluated by the shape and area of crystallization peak on thermograms with low sample maximal temperatures (Figure 3). When approaching the critical temperature, the crystallization rate reaches a minimal value. In these conditions, the amount of the melt increases with the simultaneous gradual fragmentation and melting of large crystalline residues. Sizes of the crystalline particles become close to critical value when they can still act as crystallization centers. At this point, the number of crystallization centers is maximal, and

crystallization occurs at the highest temperature (Figure 4). Melt is almost homogenous, and entropy at the system approaching its maximum value. Attachments of the atoms from the melt to the crystalline lattice of the existing crystal structure residues are complicated at these conditions. For this reason, the crystallization rate reaches its smallest value. Above these points, the crystalline phase remnants disappear in the melt, and there is a complete change in the crystallization mechanism. Instead of the gradual growth of crystalline remnants that goes practically without any activation barrier, the formation of new crystallization centers in the homogeneous liquid phase is required for the start of crystallization. The activation energy of this process is determined by the calculated above value. In all cases, after reaching the  $T_{\text{critical}}$  the crystallization rate demonstrates values in the same range  $\sim 2\text{-}3 \text{ min}^{-1}$ . These values correspond to the lowest crystallization temperatures (Figure 6b-e, Figure S3), which oscillates in the interval from 543 °C to 552 °C, as was mentioned above (Figure 4). It indicates that the cooling rate has a weak effect on the crystallization mechanism if the melt is overheated above the critical temperature. In this case, the crystallization process is determined by the homogeneous melt structure and its thermodynamic properties.



**Figure 6.** Dependencies of the CsPbBr<sub>3</sub> melt crystallization rate on the maximal sample temperature and superheating at different heating/cooling rates: a) 0.1 °C / min., b) 1 °C / min., c) 3 °C / min., d) 5 °C/min., e) 10 °C/min.

## CONCLUSION

In conclusion, we demonstrated that the melting of CsPbBr<sub>3</sub> is not an isothermal process and occurs in a defined temperature range. This range depends on heating rates and can be changed from 567-574 °C for 0.1 °C / min to 567-591 °C for 10 °C/min. The melting process of CsPbBr<sub>3</sub> occurs in two stages. The first stage is the solid phase fragmentation, and the second stage is the melting of crystalline structure residues. Using the Kissinger equation, activation energies of the melting  $E_m$  and crystallization  $E_c$  were estimated as 1846 kJ/mol and 1940 kJ/mol, respectively. We have determined the critical temperatures ( $T_{critical}$ ) for different heating/cooling rates at which the second stage of the melting process ends and the melt becomes homogeneous (579 °C for 0.1 and 1 °C/min. and 582 °C, 583 °C, 585 °C for 3, 5 and 10 °C/min respectively). In the case of heating the sample below these values, "hot" crystallization of the melt was observed. Otherwise,

if heating was continued above  $T_{\text{critical}}$ , the melt of CsPbBr<sub>3</sub> crystallized in the defined temperature range (543-552 °C, 540-550 °C, 538-543 °C, 537-542 °C and 538-542 °C for heating/cooling rates 0.1, 1, 3, 5, and 10 °C/min respectively) with almost constant supercooling. Similar dependencies were found for the melt crystallization rates with different heating/cooling rates. This study helps to understand the melting and crystallization mechanisms of CsPbBr<sub>3</sub> more deeply. Our results explain the influence of heating and cooling conditions on the melt structure of CsPbBr<sub>3</sub> and determine the temperature at which the melt becomes homogeneous. It has great significance for the growing technology of the high-quality bulk perovskite material.

#### ASSOCIATED CONTENT

##### **Supporting Information**

Photograph of the sealed quartz ampoule with the sample, Scheme of the automated DTA setup, X-ray diffraction pattern of the synthesized CsPbBr<sub>3</sub>, Dependencies of the CsPbBr<sub>3</sub> melt crystallization rate on the maximal sample temperature and the crystallization temperature.

The Supporting Information is available free of charge (PDF).

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##### **Author Contributions**

All authors have given approval to the final version of the manuscript.

##### **Notes**

The authors declare no competing financial interest.



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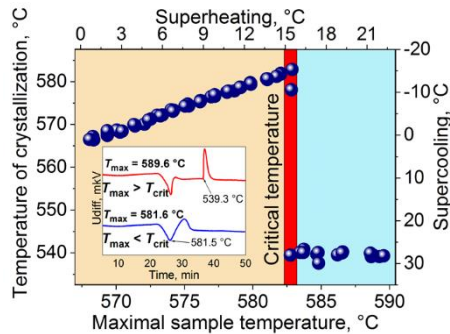
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## Melting and crystallization features of CsPbBr<sub>3</sub> perovskite

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### SYNOPSIS

We have investigated the melting and crystallization regularities of all-inorganic perovskite CsPbBr<sub>3</sub> by differential thermal analysis (DTA) with different heating/cooling rates (0.1, 1, 3, 5, and 10 °C/min). The impact of maximal sample heating temperature on the melt crystallization process has been shown. Here, we have proposed the two-stage mechanism of the CsPbBr<sub>3</sub> melting process and determined the “critical” heating temperature above which the melting process is completed. Using data from DTA-thermograms, we have evaluated activation energies of melting and crystallization processes of Cesium Lead Bromide as 1846 kJ/mol and 1940 kJ/mol, respectively.

## Supporting Information

# Melting and crystallization features of CsPbBr<sub>3</sub> perovskite

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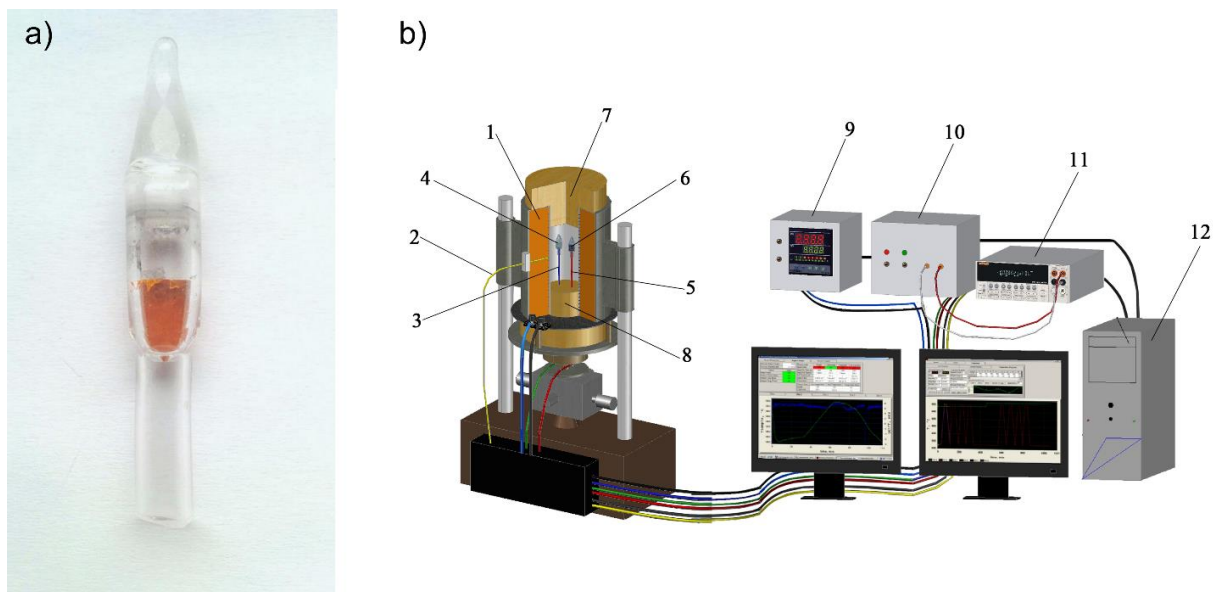
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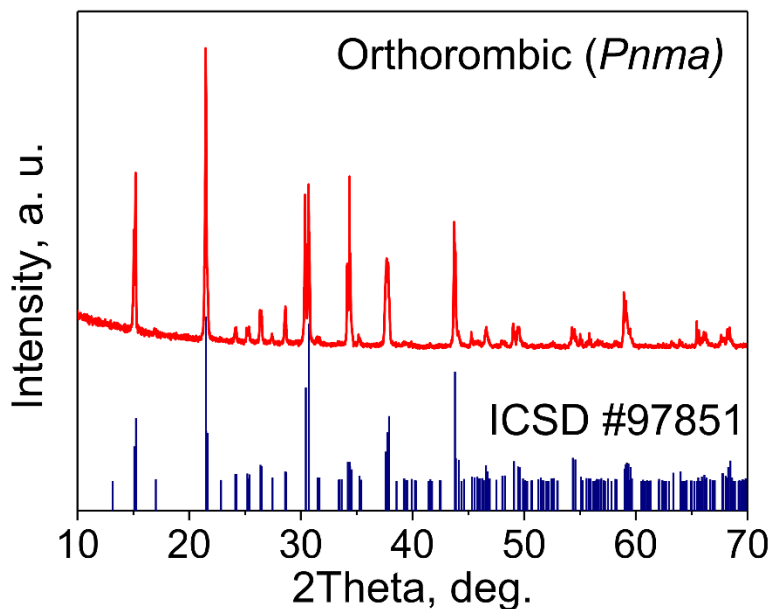
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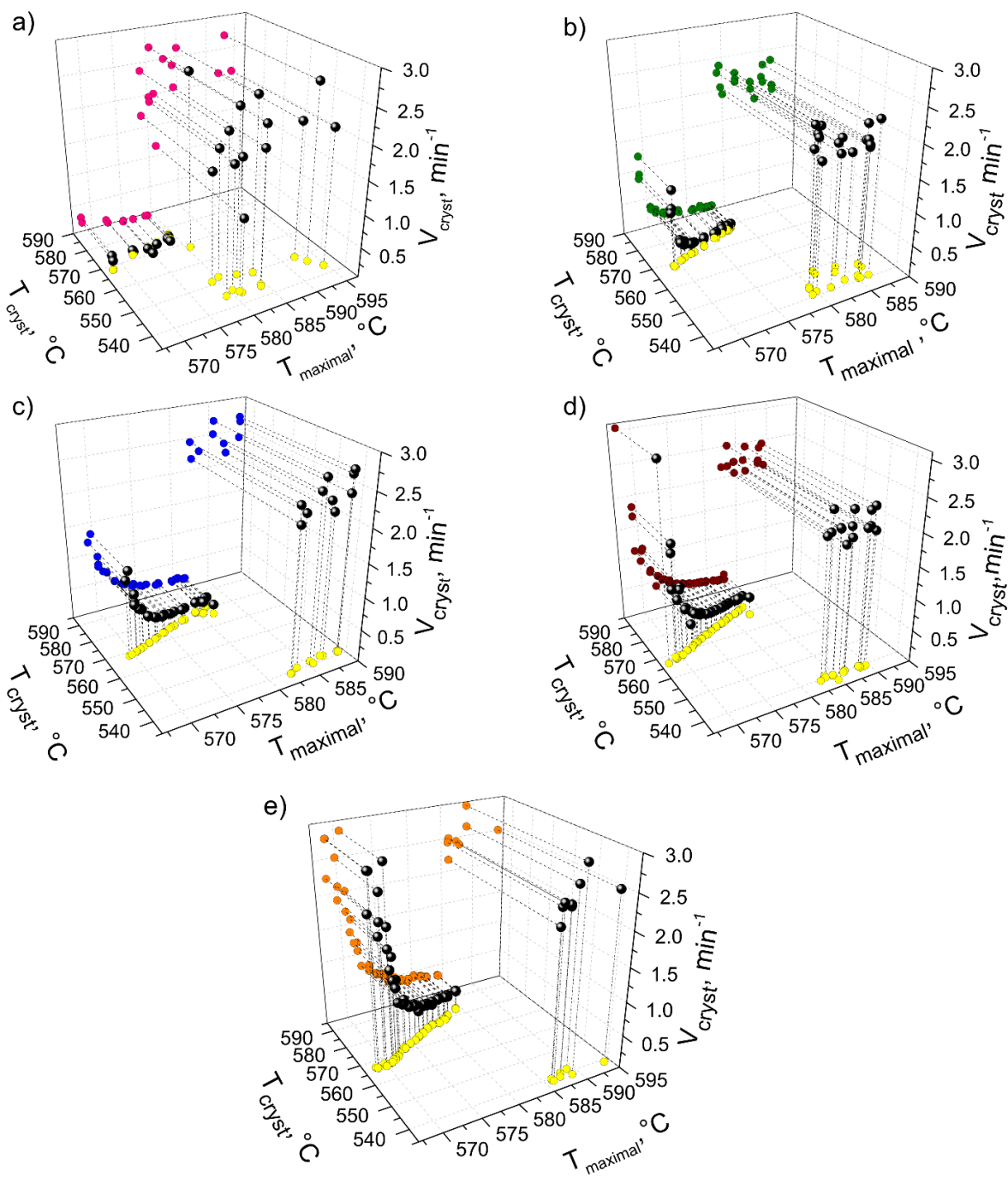


**Figure S1.** a) The sealed quartz ampoule with the sample of CsPbBr<sub>3</sub>; b) The automated DTA setup: 1 – the furnace; 2 – the thermocouple for furnace temperature control; 3 – the differential thermocouple; 4 – the ampoule with the reference sample; 5 – the thermocouple attached to the sample; 6 – the ampoule with the sample; 7, 8 – heat insulators; 9 – programmable thermocontroller Maxtermo MC2738; 10 – power unit and switchboard (scanner) of signals; 11 – universal digital multimeter Keithley 2000; 12 – computer.



**Figure S2.** X-ray diffraction pattern of the synthesized CsPbBr<sub>3</sub>. The material has an orthorhombic structure that agrees well with ICSD #97851.





**Figure S3.** Dependencies of the crystallization rate of the  $\text{CsPbBr}_3$  melt on the maximal sample temperature and the crystallization temperature at different heating/cooling rates: a) 0.1  $^{\circ}\text{C}/\text{min}$ ., b) 1  $^{\circ}\text{C}/\text{min}$ , c) 3  $^{\circ}\text{C}/\text{min}$ , d) 5  $^{\circ}\text{C}/\text{min}$ , e) 10  $^{\circ}\text{C}/\text{min}$ .

